



《风光欣》技术资料

S8050

NPN EPITAXIAL SILICON TRANSISTOR

1W OUTPUT AMPLIFIER OF PORTABLE

RADIOS IN CLASS

B PUSH-PULL OPERATION

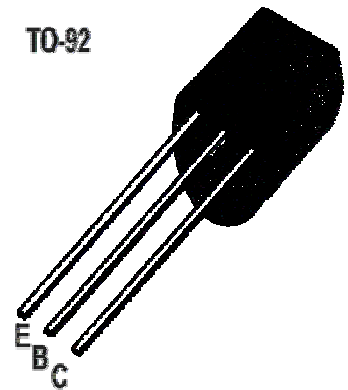
* Complimentary to S8550

* Collector Current $I_{cm} = 0.8A$

* Collector Dissipation: $P_c = 0.8W (T_c = 25)$

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EBO}	6	V
Collector Current	I_c	0.8	A
Collector Dissipation	P_c	0.8	W
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-65 ~150	



ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = 100 \mu A, I_E = 0$	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = 2mA, I_B = 0$	25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100 \mu A, I_c = 0$	6			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 35V, I_E = 0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V, I_c = 0$			100	nA
DC Current Gain	H_{FE1}	$V_{CE} = 1V, I_c = 5mA$	45	135		
	H_{FE2}	$V_{CE} = 1V, I_c = 80mA$	85	160	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = 500mA, I_B = 50mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = 500mA, I_B = 50mA$		0.98	1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 1V, I_c = 10mA$		0.66	1.0	V
Output Capacitance	C_{OB}	$f = 1MHz, V_{CB} = 10V, I_E = 0$		9		pF
Current Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_c = 50mA$	100	190		MHz

HFE(2) CLASSIFICATION

Classification	B	C	D	E	F
$H_{FE(2)}$	85-160	120-200	160-300	300-400	400-500